



#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max                        | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|--|--|
| 2014              | $350 \text{m}\Omega$ @ $V_{GS} = -10 \text{V}$ | -1.5A  |
| -60V              | 550mΩ @ V <sub>GS</sub> = -4.5V                | -1.2A  |

## **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

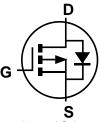
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

#### **Mechanical Data**

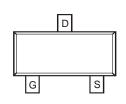
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)











Top View

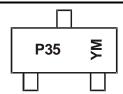
### Ordering Information (Note 5)

| Part Number  | Case  | Packaging          |
|--------------|-------|--------------------|
| DMP6350SQ-7  | SOT23 | 3000/Tape & Reel   |
| DMP6350SQ-13 | SOT23 | 10,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



P35 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$ = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Kev

| Date Code ite |      |      |      |      |      |      |      |      |
|---------------|------|------|------|------|------|------|------|------|
| Year          | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 |
| Code          | С    | D    | E    | F    | G    | Н    | I    | J    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | 0   | N   | D   |



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                | Symbol          | Value     | Unit |   |
|---|----------------|-----------------|-----------|------|---|
| Drain-Source Voltage                                      |                |                 | $V_{DSS}$ | -60  | V |
| Gate-Source Voltage                                       |                |                 | $V_{GSS}$ | ±20  | V |
| Continuous Drain Current (Note 7), V <sub>GS</sub> = -10V | I <sub>D</sub> | -1.5<br>-1.2    | А         |      |   |
| Pulsed Drain Current (10µs Pulse, Duty Cycle =            | 1%)            | I <sub>DM</sub> | -6        | Α    |   |

# **Thermal Characteristics**

| Characteristic   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 6)   | P <sub>D</sub>                    | 0.72        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6) | $R_{	heta JA}$                    | 176         | °C/W |
| Power Dissipation (Note 7)   | P <sub>D</sub>                    | 1.17        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7) | $R_{	heta JA}$                    | 108         | °C/W |
| Thermal Resistance, Junction to Case                                     | $R_{	heta JC}$                    | 34          | °C/W |
| Operating and Storage Temperature Range                                  | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

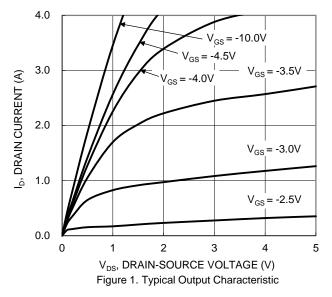
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

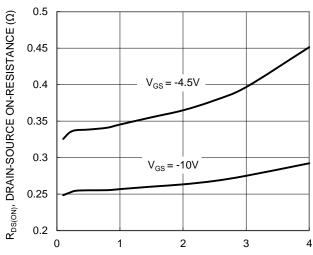
| Characteristic   | Symbol              | Min  | Тур  | Max  | Unit     | Test Condition   |  |
|--|---------------------|------|------|------|----------|--|--|
| OFF CHARACTERISTICS (Note 8)                           |                     |      |      |      |          |  |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | -60  | _    | _    | V        | $V_{GS} = 0V, I_D = -250\mu A$                                   |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | _    | _    | -1.0 | μΑ       | $V_{DS} = -60V, V_{GS} = 0V$                                     |  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | _    | _    | ±100 | nA       | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                               |  |
| ON CHARACTERISTICS (Note 8)                            |                     |      |      |      |          |  |  |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | -1.0 | -1.8 | -3.0 | <b>V</b> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                            |  |
| Static Drain-Source On-Resistance                      | D                   |      | 257  | 350  | mΩ       | $V_{GS} = -10V, I_D = -0.9A$                                     |  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | _    | 343  | 550  | 11122    | $V_{GS} = -4.5V$ , $I_{D} = -0.8A$                               |  |
| Diode Forward Voltage                                  | $V_{SD}$            | _    | -0.8 | -1.2 | <b>V</b> | $V_{GS} = 0V$ , $I_S = -1A$                                      |  |
| DYNAMIC CHARACTERISTICS (Note 9)                       |                     |      |      |      |          |  |  |
| Input Capacitance                                      | C <sub>iss</sub>    | _    | 206  |      | рF       | .,   |  |
| Output Capacitance                                     | Coss                | _    | 15   | _    | pF       | $V_{DS} = -30V, V_{GS} = 0V,$<br>- f = 1.0MHz                    |  |
| Reverse Transfer Capacitance                           | Crss                | _    | 11   |      | рF       | T = 1.0WH IZ   |  |
| Gate Resistance  | Rg                  | _    | 17   | _    | Ω        | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                       |  |
| Total Gate Charge (V <sub>GS</sub> = -4.5V)            | $Q_{g}$             | _    | 2.0  |      | nC       |  |  |
| Total Gate Charge (V <sub>GS</sub> = -10V)             | Qg                  | _    | 4.1  | _    | nC       | N 201/ 1 0 0 0   |  |
| Gate-Source Charge                                     | $Q_{gs}$            |      | 0.5  |      | nC       | $V_{DS} = -30V, I_{D} = -0.9A$                                   |  |
| Gate-Drain Charge                                      | $Q_{gd}$            | _    | 0.8  | _    | nC       |  |  |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | _    | 3.6  | _    | ns       |  |  |
| Turn-On Rise Time                                      | t <sub>R</sub>      | _    | 3.8  | _    | ns       | $V_{DD} = -30V, V_{GS} = -10V,$ $I_{D} = -1.0A, R_{g} = 6\Omega$ |  |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> | _    | 12.3 | _    | ns       |  |  |
| Turn-Off Fall Time                                     | t <sub>F</sub>      | _    | 7.3  | _    | ns       | 7  |  |
| Body Diode Reverse Recovery Time                       | t <sub>RR</sub>     | _    | 8.2  | _    | ns       | $I_S = -1.0A$ , di/dt = -100A/ $\mu$ s                           |  |
| Body Diode Reverse Recovery Charge                     | Q <sub>RR</sub>     | _    | 2.7  | _    | nC       | $I_S = -1.0A$ , di/dt = -100A/ $\mu$ s                           |  |

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

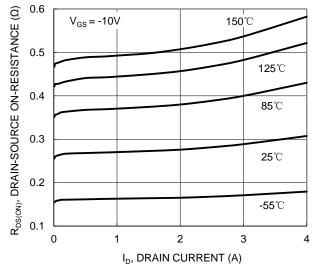
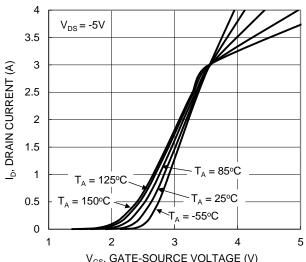


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

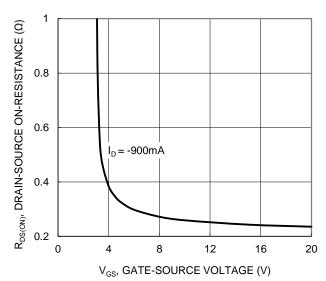


Figure 4. Typical Transfer Characteristic

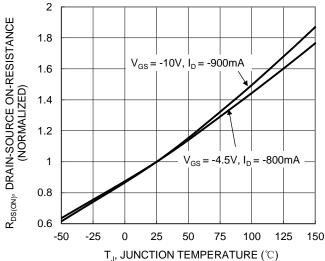


Figure 6. On-Resistance Variation with Junction Temperature



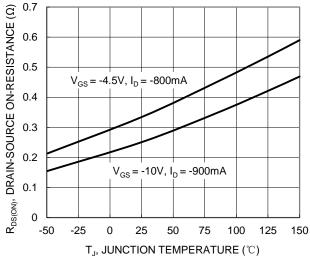
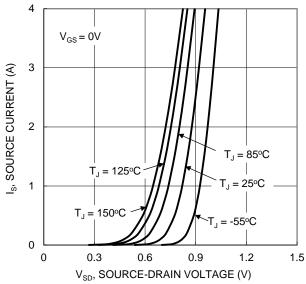
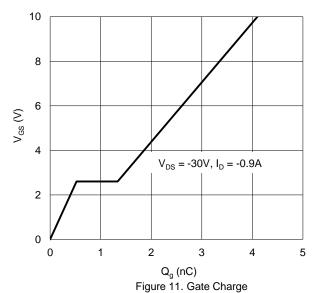


Figure 7. On-Resistance Variation with Junction
Temperature

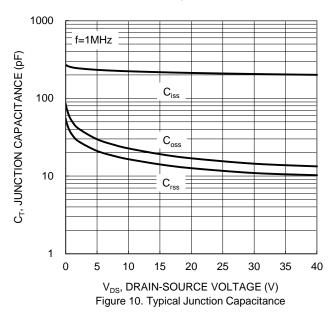


V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



2.2  $V_{\text{GS}(TH)}, \text{ GATE THRESHOLD VOLTAGE }(V)$ 2  $I_D = -1mA$ 1.8  $I_{D} = -250 \mu A$ 1.6 1.4 1.2 -50 -25 25 50 75 100 125 150

T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature



 $\begin{array}{c} 10 \\ R_{DS(ON)} \text{ Limited} \\ P_W = 100 \mu \text{s} \\ \hline \\ 0.01 \\ P_W = 10 \text{ms} \\ \hline \\ P_W =$ 

Figure 12. SOA, Safe Operation Area



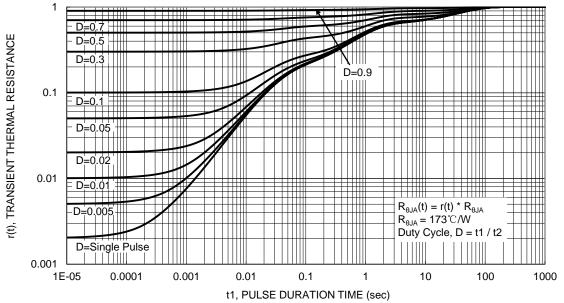
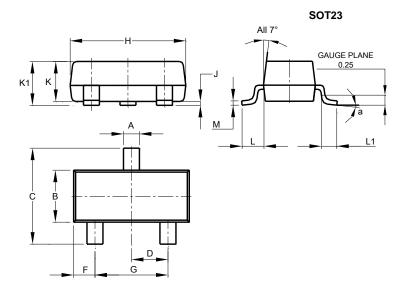


Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

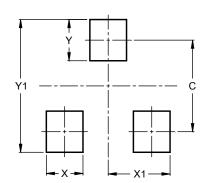
Please see http://www.diodes.com/package-outlines.html for the latest version.



|     | SOT23                |       |       |  |  |  |  |  |  |  |
|-----|----------------------|-------|-------|--|--|--|--|--|--|--|
| Dim | Min                  | Max   | Тур   |  |  |  |  |  |  |  |
| Α   | 0.37                 | 0.51  | 0.40  |  |  |  |  |  |  |  |
| В   | 1.20                 | 1.40  | 1.30  |  |  |  |  |  |  |  |
| С   | 2.30                 | 2.50  | 2.40  |  |  |  |  |  |  |  |
| D   | 0.89                 | 1.03  | 0.915 |  |  |  |  |  |  |  |
| F   | 0.45                 | 0.60  | 0.535 |  |  |  |  |  |  |  |
| G   | 1.78                 | 2.05  | 1.83  |  |  |  |  |  |  |  |
| Н   | 2.80                 | 3.00  | 2.90  |  |  |  |  |  |  |  |
| J   | 0.013                | 0.10  | 0.05  |  |  |  |  |  |  |  |
| K   | 0.890                | 1.00  | 0.975 |  |  |  |  |  |  |  |
| K1  | 0.903                | 1.10  | 1.025 |  |  |  |  |  |  |  |
| ٦   | 0.45                 | 0.61  | 0.55  |  |  |  |  |  |  |  |
| L1  | 0.25                 | 0.55  | 0.40  |  |  |  |  |  |  |  |
| M   | 0.085                | 0.150 | 0.110 |  |  |  |  |  |  |  |
| а   | 0°                   | 8°    |       |  |  |  |  |  |  |  |
| All | All Dimensions in mm |       |       |  |  |  |  |  |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT23

| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Υ          | 0.9           |
| Y1         | 2.9           |

July 2018



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